

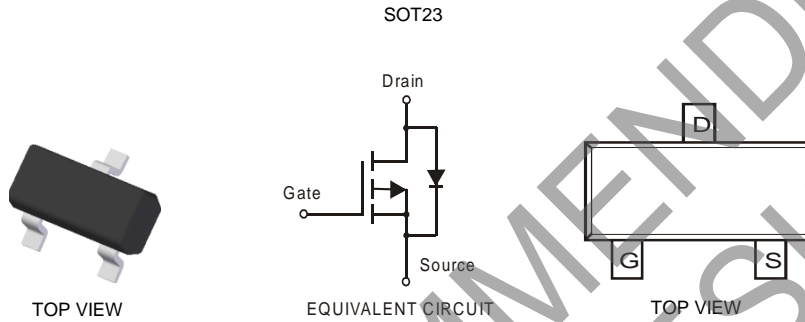
**P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

**Features**

- Low On-Resistance:
  - $R_{DS(ON)} < 100m\Omega @ V_{GS} = -4.5V, I_D = -2.7A$
  - $R_{DS(ON)} < 215m\Omega @ V_{GS} = -2.5V, I_D = -2.0A$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

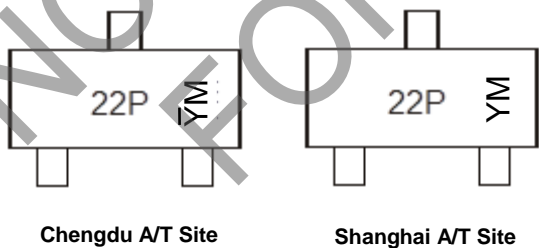


**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP2215L-7	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>

**Marking Information**



22P = Product Type Marking Code  
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test Site)  
 Y̅M = Date Code Marking for CAT (Chengdu Assembly/ Test Site)  
 Y or Y̅ = Year (ex: E = 2017)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-2.7 -2	A
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-8	A

### Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)			R <sub>θJA</sub>	115	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-800	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
On-State Drain Current	I <sub>D(ON)</sub>	-6 -3	—	—	A	V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> = -4.5V V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> = -2.5V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±80	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.45	—	-1.25	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	80 165	100 215	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.7A V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	4	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.7A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	—	-1.26	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.7A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	250	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	88	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	58	—	pF	
Gate Resistance	R <sub>g</sub>	—	12	16	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	4.3	5.3	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.9	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.1	—		

- Notes:
5. Device mounted on FR-4 PCB. t ≤ 5 sec.
  6. Pulse width ≤ 10μs, Duty Cycle ≤ 1%.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

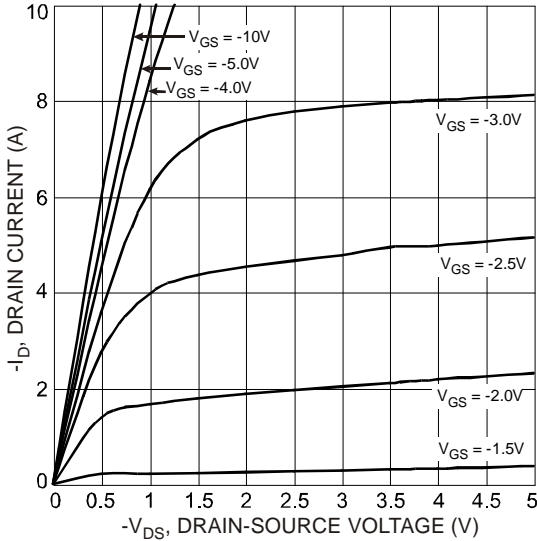


Fig. 1 Typical Output Characteristics

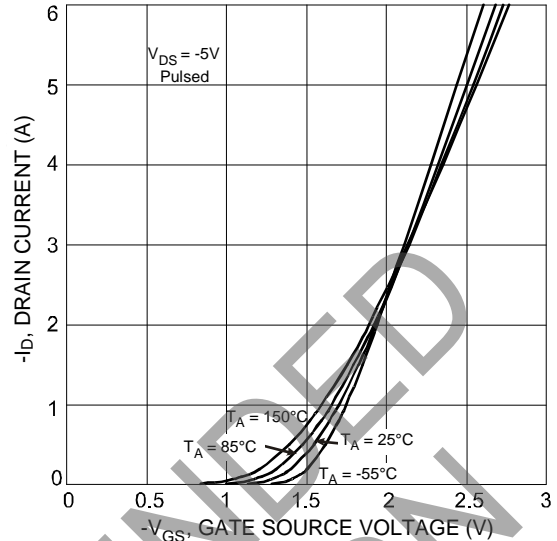


Fig. 2 Typical Transfer Characteristics

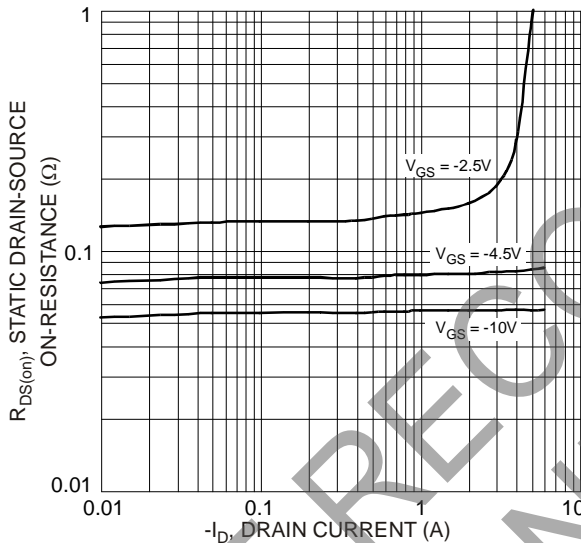


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

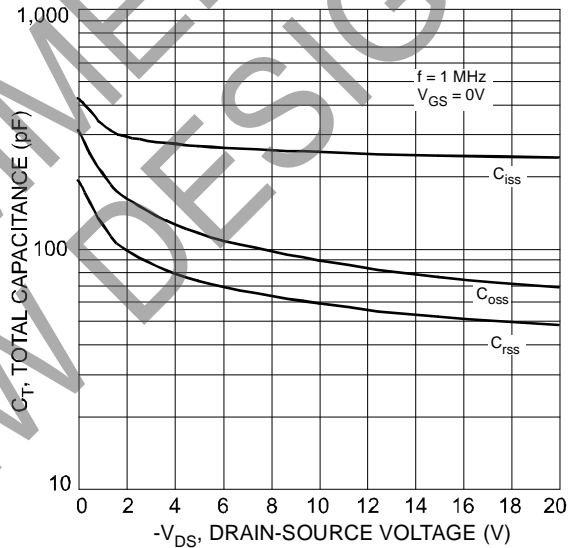


Fig. 4 Typical Total Capacitance

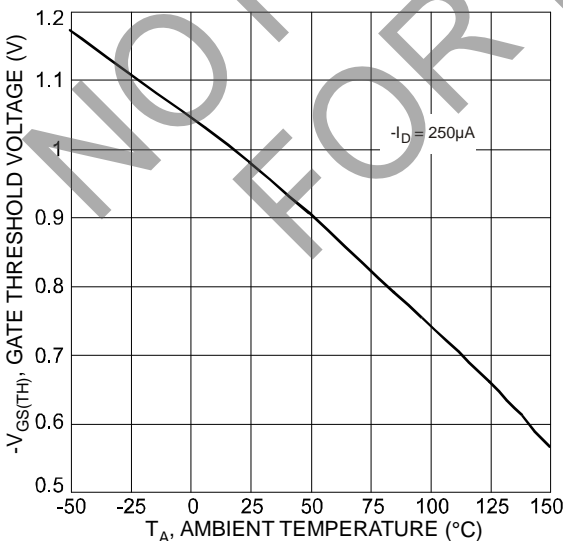


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

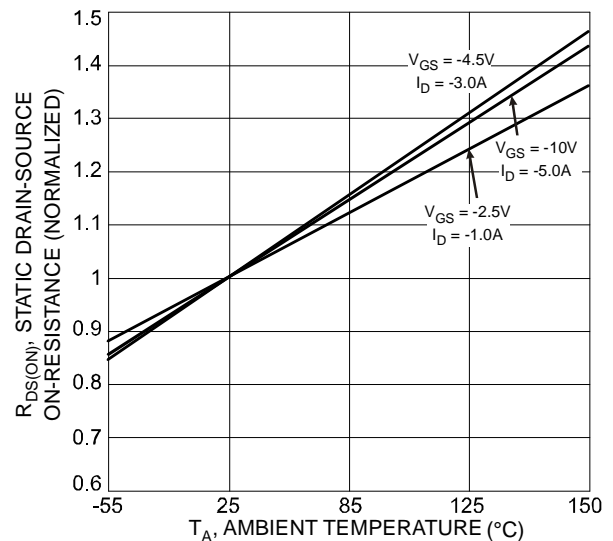


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

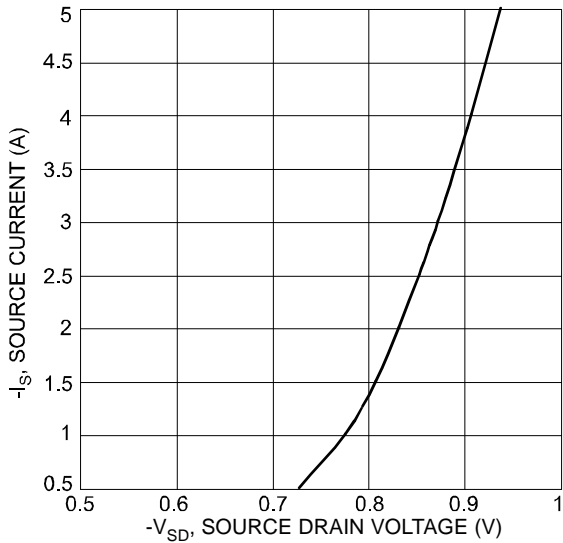
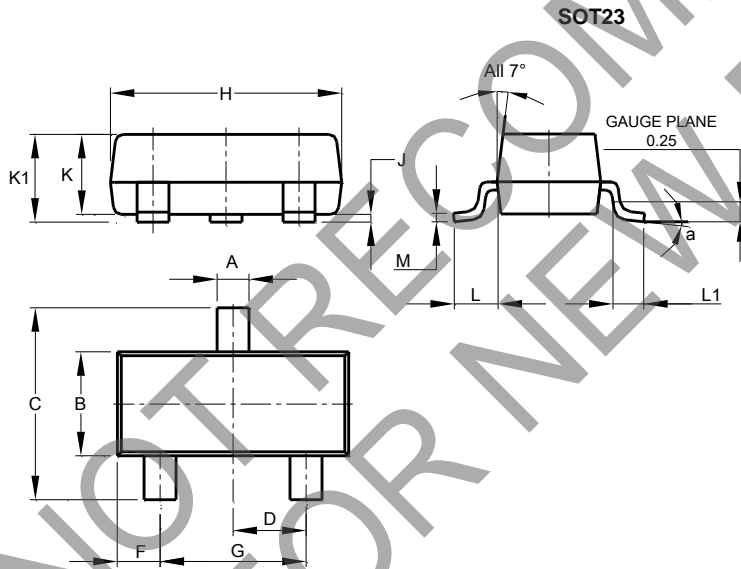


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

### Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

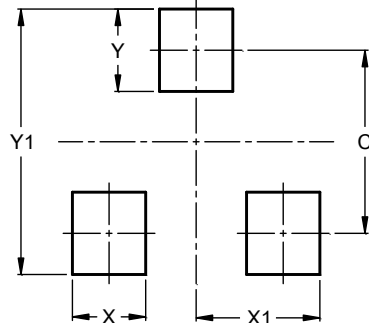


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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